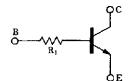


# COMPOUND TRANSISTOR AA1L4Z

# on-chip resistor NPN silicon epitaxial transistor For mid-speed switching

#### **FEATURES**

 On-chip bias resistor (R<sub>1</sub> = 47 kΩ)



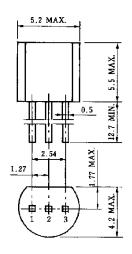
· Complementary transistor with AN1L4Z

## ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	Vcво	60	V	
Collector to emitter voltage	VCEO	50	V	
Emitter to base voltage	V <sub>EBO</sub>	5	V	
Collector current (DC)	Ic(DC)	100	mA	
Collector current (Pulse)	Ic(pulse) *	200	mA	
Total power dissipation	Рт	250	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

<sup>\*</sup> PW  $\leq$  10 ms, duty cycle  $\leq$  50 %

#### PACKAGE DRAWING (UNIT: mm)



Electrode Connection

Emitter EIAJ : SC-43B
 Collector JEDEC : TO-92
 Base IEC : PA33

# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0			100	nA
DC current gain	h <sub>FE1</sub> **	VcE = 5.0 V, Ic = 5.0 mA	135	270	600	-
DC current gain	h <sub>FE2</sub> **	VcE = 5.0 V, Ic = 50 mA	100	260		-
Collector saturation voltage	V <sub>CE(sat)</sub> **	Ic = 5.0 mA, I <sub>B</sub> = 0.25 mA		0.05	0.2	V
Low level input voltage	VIL **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \ \mu\text{A}$		0.57	0.5	V
High level input voltage	V <sub>IH</sub> **	VcE = 0.2 V, Ic = 5.0 mA	4.0	1.7		V
Input resistance	R <sub>1</sub>		32.9	47	61.1	kΩ
Turn-on time	ton	$V$ cc = 5.0 $V$ , $R$ L = 1.0 $k\Omega$			0.2	μs
Storage time	<b>t</b> stg	$V_1 = 5.0 \text{ V}, \text{ PW} = 2.0 \ \mu\text{s}$			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

<sup>\*\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %

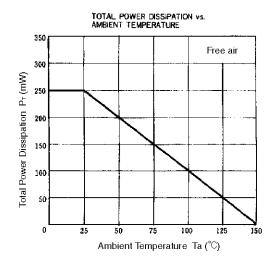
### **hfe CLASSIFICATION**

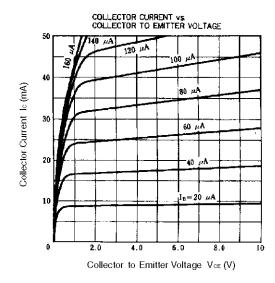
Marking	Q	Р	К
h <sub>FE1</sub>	135 to 270	200 to 400	300 to 600

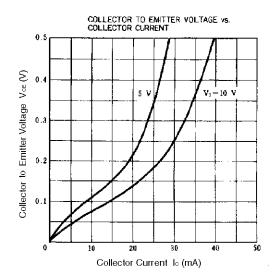
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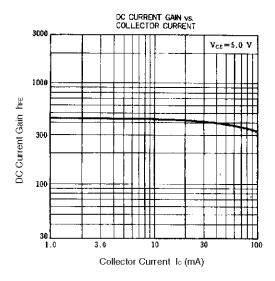


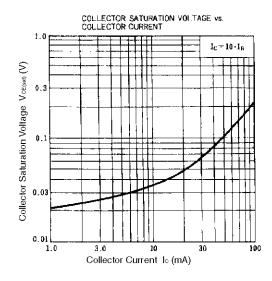
# TYPICAL CHARACTERISTICS (Ta = 25°C)

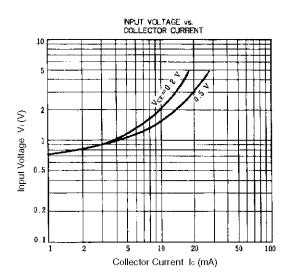


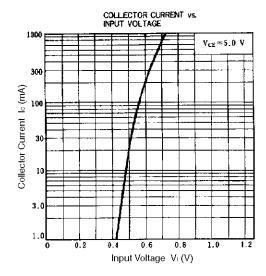


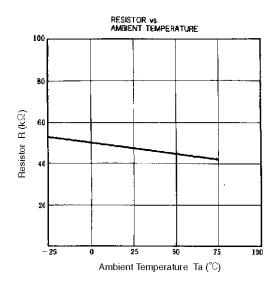












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